# CPC COOPERATIVE PATENT CLASSIFICATION

## G PHYSICS

(NOTES omitted)

### **INSTRUMENTS**

### G02 OPTICS

(NOTE omitted)

# OPTICAL DEVICES OR ARRANGEMENTS FOR THE CONTROL OF LIGHT BY MODIFICATION OF THE OPTICAL PROPERTIES OF THE MEDIA OF THE ELEMENTS INVOLVED THEREIN; NON-LINEAR OPTICS; FREQUENCY-CHANGING OF LIGHT; OPTICAL LOGIC ELEMENTS; OPTICAL ANALOGUE/DIGITAL CONVERTERS

#### WARNINGS

1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups:

Subject matter covered by these groups is classified in the following CPC groups:

G02F 1/13357 covered by G02F 1/1336 and subgroups

2. In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

1/00	Devices or arrangements for the control of the
	intensity, colour, phase, polarisation or direction
	of light arriving from an independent light source,
	e.g. switching, gating or modulating; Non-linear
	optics

### NOTE

This group covers only:

- devices or arrangements, e.g. cells, the optical operation of which is modified by changing the optical properties of the medium of the devices or arrangements by the influence or control of physical parameters, e.g. electric fields, electric current, magnetic fields, sound or mechanical vibrations, stress or thermal effects;
- devices or arrangements in which the electric or magnetic field component of the light beams influences the optical properties of the medium, i.e. non-linear optics;
- control of light by electromagnetic waves, e.g. radio waves, or by electrons or other elementary particles.

1/0009 • {Materials therefor}

## **NOTE**

 $\underline{\text{G02F 1/0009}}$  and subgroups contain mostly nonpatent literature

1/0018 . . {Electro-optical materials}
1/0027 . . . {Ferro-electric materials}
1/0036 . . {Magneto-optical materials}

1/0045 • • {Liquid crystals characterised by their physical properties}

1/0054 • • {Structure, phase transitions, NMR, ESR, Moessbauer spectra}

1/0063 • • {Optical properties, e.g. absorption, reflection or birefringence (materials for non-linear optics G02F 1/355)}

1/0072 • {Mechanical, acoustic, electro-elastic, magnetoelastic properties}

1/0081 . . {Electric or magnetic properties}

1/009 . . {Thermal properties}

1/01 • for the control of the intensity, phase, polarisation or colour (G02F 1/29, G02F 1/35 take precedence)

1/0102 • {Constructional details, not otherwise provided for in this subclass}

1/0105 . . . {Illuminating devices}

1/0107 • • • {Gaskets, spacers or sealing of cells; Filling and closing of cells}

1/011 • { in optical waveguides, not otherwise provided for in this subclass }

 $\begin{array}{cccc} 1/0113 & \dots & \{Glass\text{-based, e.g. silica-based, optical} \\ & & waveguides \} \end{array}$ 

1/0115 . . . {in optical fibres}

1/0118 . . . . {by controlling the evanescent coupling of light from a fibre into an active, e.g. electrooptic, overlay}

1/0121 • • {Operation of devices; Circuit arrangements, not otherwise provided for in this subclass}

1/0123 • • • {Circuits for the control or stabilisation of the bias voltage, e.g. automatic bias control [ABC] feedback loops}

1/0126 • • {Opto-optical modulation, i.e. control of one light beam by another light beam, not otherwise provided for in this subclass}

1/0128 . . {based on electro-mechanical, magneto-mechanical, elasto-optic effects}

1/0131 . . . {based on photo-elastic effects, e.g. mechanically induced birefringence}

1/0134 . . . . {in optical waveguides}

1/0136	• • {for the control of polarisation, e.g. state of polarisation [SOP] control, polarisation	1/0333 { addressed by a beam of charged particles (G02F 1/05 takes precedence)}
	scrambling, TE-TM mode conversion or separation (G02F 1/0353 takes precedence)}	1/0338 • • • { structurally associated with a photoconductive layer or having photo-refractive properties
1/0139	• • • {Polarisation scrambling devices;	$(\underline{G02F 1/05} \text{ takes precedence})$
1/01/12	Depolarisers}	1/0344 {controlled by a high-frequency
1/0142	{TE-TM mode conversion}	electromagnetic wave component in an
1/0144	{TE-TM mode separation}	electric waveguide ( <u>G02F 1/0356</u> , <u>G02F 1/05</u> , <u>G02F 1/2255</u> , <u>G02F 1/3134</u> take precedence)}
1/0147	• • {based on thermo-optic effects (G02F 1/132 takes precedence)}	1/035 in an optical waveguide structure
1/015	based on semiconductor elements having potential barriers, e.g. having a PN or PIN	1/0353 {involving an electro-optic TE-TM mode conversion}
	junction ( <u>G02F 1/03</u> takes precedence)	1/0356 {controlled by a high-frequency
1/0151	• • • {modulating the refractive index}	electromagnetic wave component in an
1/0152	• • • {using free carrier effects, e.g. plasma effect}	electric waveguide structure}
1/0153	• • • {using electro-refraction, e.g. Kramers-	1/05 with ferro-electric properties (G02F 1/035,
	Kronig relation}	G02F 1/055 take precedence)
1/0154	• • • {using electro-optic effects, e.g. linear	1/0508 {specially adapted for gating or modulating
	electro optic [LEO], Pockels, quadratic	in optical waveguides}
	electro optical [QEO] or Kerr effect}	1/0516 {Operation of the cell; Circuit arrangements}
1/0155	• • { modulating the optical absorption}	1/0525 • • • • {addressed by a beam of charged particles}
1/0156	• • • {using free carrier absorption}	1/0533 { structurally associated with a photo-
1/0157	• • • • {using electro-absorption effects, e.g. Franz-	conductive layer}
	Keldysh [FK] effect or quantum confined	1/0541 • • • • {using photorefractive effects}
	stark effect [QCSE]}	1/055 the active material being a ceramic
1/0158	• • • • {Blue-shift of the absorption band}	(G02F 1/035 takes precedence)
1/0159	• • • • {Red-shift of the absorption band}	1/0551 {Constructional details}
1/017	Structures with periodic or quasi periodic	1/0553 {specially adapted for gating or modulating
	potential variation, e.g. superlattices, quantum	in optical waveguides}
	wells	1/0555 {Operation of the cell; Circuit arrangements}
1/01708	{in an optical wavequide structure}	1/0556 {specially adapted for a particular
1/01716	{Optically controlled superlattice or quantum	application}
	well devices}	1/0558 {structurally associated with a
1/01725	• • • {Non-rectangular quantum well structures, e.g. graded or stepped quantum wells}	photoconductive layer or exhibiting photo- refractive properties}
1/01733	• • • • {Coupled or double quantum wells}	1/061 based on electro-optical organic material
1/01741	{Asymmetrically coupled or double	$(\underline{G02F 1/07}, \{\underline{G02F 1/13}\} \text{ take precedence})$
	quantum wells}	1/065 in an optical waveguide structure
1/0175	• • • • { with a spatially varied well profile, e.g.	1/07 based on electro-optical liquids exhibiting Kerr
	graded or stepped quantum wells}	effect
1/01758	• • • • • { with an asymmetric well profile, e.g. asymmetrically stepped quantum wells}	1/073 {specially adapted for gating or modulating in optical waveguides}
1/01766	{Strained superlattice devices; Strained	1/076 • • • {Operation of the cell; Circuit arrangements}
	quantum well devices}	1/09 based on magneto-optical elements, e.g.
1/01775	• • • { involving an inter-subband transition in one	exhibiting Faraday effect
1/01783	well, e.g. e1->e2} {Quantum wires}	1/091 {based on magneto-absorption or magneto-reflection}
1/01791	{Quantum boxes or quantum dots}	1/092 {Operation of the cell; Circuit arrangements}
1/01/51	in an optical waveguide structure (G02F 1/017,	1/093 {used as non-reciprocal devices, e.g. optical
	$\{\underline{\text{G02F }1/2257}\}\ $ take precedence)	isolators, circulators (G02F 1/0955 takes precedence)}
1/03	based on ceramics or electro-optical crystals,     e.g. exhibiting Pockels effect or Kerr effect	1/094 {based on magnetophoretic effect}
	(G02F 1/061 takes precedence)	1/095 in an optical waveguide structure
1/0205	• • {Constructional arrangements	
1/0305	(G02F 1/0327 - G02F 1/05 take precedence)	1/0955 { used as non-reciprocal devices, e.g. optical isolators, circulators}
1/0211	• • • {Structural association of optical elements,	
1/0311	e.g. lenses, polarizers, phase plates, with the crystal}	1/11 • based on acousto-optical elements, e.g. using variable diffraction by sound or like mechanical waves (acousto-optical deflection G02F 1/33)
1/0316	• • • {Electrodes}	1/113 {Circuit or control arrangements}
1/0310	{Arrangements comprising two or more	1/116 {using an optically anisotropic medium,
1/0322	independently controlled crystals}	wherein the incident and the diffracted
1/0327	• • • {Operation of the cell; Circuit arrangements	light waves have different polarizations,
1,0521	(G02F 1/05 takes precedence)	e.g. acousto-optic tunable filter [AOTF]
	(/)	(G02F 1/125 takes precedence)}

1/125 in a	n optical waveguide structure	1/13335/				{Arrangements for aligning or assembling
	on liquid crystals, e.g. single liquid crystal	1/133334		•		substrates}
	y cells	1/133357		_		{Planarisation layers}
_	pparatus specially adapted to the					{Combining plural substrates to produce
	nufacture of LCDs}	1,13330		•		large-area displays, e.g. tiled displays}
1/1306 {De		1/133362				Optically addressed liquid crystal cells
	Repairing; Testing}					(G02F 1/135 takes precedence)}
	ecially adapted for a particular application}	1/133365				{Cells in which the active layer comprises
	ethods for cleaning the liquid crystal cells,					a liquid crystalline polymer}
	components thereof, during manufacture:	1/133368				{Cells having two substrates with different
Ma	terials therefor}					characteristics, e.g. different thickness or
	nermal activation of liquid crystals					material}
	ibiting a thermo-optic effect}	1/133371		•		{Cells with varying thickness of the liquid
	rrangements for providing a switchable	1/122274				crystal layer}
	wing angle}					{for displaying permanent signs or marks}
	quid crystal optical waveguides or liquid	1/1333//		•		{Cells with plural compartments or having plurality of liquid crystal microcells
	stal cells specially adapted for gating or dulating between optical waveguides}					partitioned by walls, e.g. one microcell per
	nstructional arrangements; Operation of					pixel}
	id crystal cells; Circuit arrangements	1/13338				{Input devices, e.g. touch panels}
	rangements or circuits for control of liquid					{Heating or cooling of liquid crystal cells
	stal elements in a matrix, not structurally	1,100002		•		other than for activation, e.g. circuits or
	ociated with these elements G09G 3/36)					arrangements for temperature control,
1/13306 {	Circuit arrangements or driving methods					stabilisation or uniform distribution over
	or the control of single liquid crystal					the cell}
	ells ( <u>G02F 1/132</u> , <u>G02F 1/133382</u> take					• {with cooling means, e.g. fans}
	recedence)}	1/133388		•		{with constructional differences between
1/13312	{Circuits comprising photodetectors for					the display region and the peripheral
1/12210	purposes other than feedback}	1/100001				region}
	{Circuits comprising a photodetector}	1/133391		•		{Constructional arrangement for sub-
	{Circuits comprising solar cells}	1/122204				divided displays}
	Constructional arrangements;	1/133394	• • •	•		{Piezoelectric elements associated with the cells}
	Manufacturing methods}(G02F 1/135, G02F 1/136 take precedence)	1/133307				{for suppressing after-image or image-
	{Rigid substrates, e.g. inorganic	1/133377		•		sticking}
1/133302	substrates}	1/1334				based on polymer dispersed liquid crystals,
1/133305	{Flexible substrates, e.g. plastics, organic					e.g. microencapsulated liquid crystals
	film}	1/13342				• {Holographic polymer dispersed liquid
1/133308	{Support structures for LCD panels, e.g.					crystals}
	frames or bezels}					• {Network or three-dimensional gels}
1/133311	• {Environmental protection, e.g. against	1/13347		•		• {working in reverse mode, i.e. clear in
	dust or humidity}					the off-state and scattering in the on-
1/133314						state}
1/133317	• {Intermediate frames, e.g. between	1/1335		•		Structural association of cells with optical
1/10000	backlight housing and front frame}	1/122502				devices, e.g. polarisers or reflectors
1/13332		1/133502	• • •	•	•	• {Antiglare, refractive index matching layers}
1/133322	• {Mechanical guidance or alignment of	1/133504				• {Diffusing, scattering, diffracting
1/122225	LCD panel support components} • {Assembling processes}	1/133304	• • •	•	•	elements (associated to illuminating
						devices <u>G02F 1/133606</u> )}
1/133328	• {Segmented frames}	1/133507				• • {Films for enhancing the luminance}
	• {Cover glasses} • {Electromagnetic shields}					• {Filters, e.g. light shielding masks}
	{Layers preventing ion diffusion, e.g. by					• • {Light shielding layers, e.g. black
1/133337 • • • • •	ion absorption}		. •	-		matrix ( <u>G02F 1/136209</u> takes
1/13334	{Plasma addressed liquid crystal cells					precedence)}
1/1000T	[PALC]}	1/133514				• • {Colour filters}
1/133342	{for double-sided displays}	1/133516		•		• • • {Methods for their manufacture,
	{Insulating layers (G02F 1/1335,					e.g. printing, electro-deposition or
	G02F 1/1337, G02F 1/135, G02F 1/136					photolithography}
	take precedence)}					• • • {Overcoatings}
1/133348	{Charged particles addressed liquid crystal					{Interference filters}
	cells, e.g. controlled by an electron beam}	1/133524		•	•	• {Light-guides, e.g. fibre-optic bundles,
1/133351	{Manufacturing of individual cells out of a					louvered or jalousie light-guides}
	plurality of cells, e.g. by dicing}					

1/133526 {Lenses, e.g. microlenses or Fresnel	1/133621 {providing coloured light
lenses}	(G02F 1/133617, G02F 1/133533 take
1/133528 {Polarisers}	precedence)}
1/133531 {characterised by the arrangement of	1/133622 {Colour sequential illumination}
polariser or analyser axes}	1/133623 {Inclined coloured light beams}
1/133533 {Colour selective polarisers (G02F 1/1347 takes precedence)}	1/133624 {characterised by their spectral emissions}
1/133536 {Reflective polarizers ( <u>G02F 1/13362</u>	1/133625 {Electron stream lamps}
takes precedence)}	1/133626 · · · · · · · {providing two modes of
1/133538 { with spatial distribution of the	illumination, e.g. day-night}
polarisation direction}	1/133627 {Projection-direct viewing}
1/133541 {Circular polarisers}	1/133628 · · · · · · {with cooling means}
1/133543 {Cholesteric polarisers}	1/13363 Birefringent elements, e.g. for optical
1/133545 {Dielectric stack polarisers}	compensation
1/133548 {Wire-grid polarisers}	1/133631 {with a spatial distribution of the
1/13355 {Polarising beam splitters [PBS]}	retardation value}
1/133553 {Reflecting elements (associated to	1/133632 { with refractive index ellipsoid
illuminating devices <u>G02F 1/133605</u> )}	inclined relative to the LC-layer
1/133555 {Transflectors}	surface}
1/133557 {Half-mirrors}	1/133633 {using mesogenic materials}
1/13356 {characterised by the placement of the	1/133634 { the refractive index Nz perpendicular
optical elements}	to the element surface being different from in-plane refractive indices Nx
$1/133562 \dots \dots $ {on the viewer side}	and Ny, e.g. biaxial or with normal
1/133565 {inside the LC elements, i.e. between	optical axis}
the cell substrates}	1/133635 {Multifunctional compensators}
1/133567 {on the back side}	1/133636 {with twisted orientation, e.g.
1/1336 {Illuminating devices}	comprising helically oriented LC-
1/133601 {for spatial active dimming}	molecules or a plurality of twisted
1/133602 {Direct backlight}	birefringent sublayers}
1/133603 {with LEDs}	1/133637 {characterised by the wavelength
1/133604 { with lamps}	dispersion}
1/133605 { including specially adapted reflectors}	1/133638 {Waveplates, i.e. plates with a
1/133606 {including a specially adapted	retardation value of lambda/n}
diffusing, scattering or light	1/1337 Surface-induced orientation of the liquid
controlling members}	crystal molecules, e.g. by alignment layers
1/133607 {the light controlling member	1/133703 • • • • • {by introducing organic surfactant additives into the liquid crystal
including light directing or	material}
refracting elements, e.g. prisms	1/133707 Structures for producing distorted
or lenses}	electric fields, e.g. bumps, protrusions,
1/133608 {including particular frames or	recesses, slits in pixel electrodes}
supporting means}	1/133711 {by organic films, e.g. polymeric films}
1/133609 { including means for improving the color mixing, e.g. white}	1/133715 {by first depositing a monomer}
1/133611 { including means for improving the	1/133719 {with coupling agent molecules, e.g.
brightness uniformity}	silane}
1/133612 {Electrical details}	1/133723 {Polyimide, polyamide-imide}
1/133613 {characterized by the sequence of	1/133726 {made of a mesogenic material}
light sources}	1/13373 {Disclination line; Reverse tilt}
1/133614 { using photoluminescence, e.g.	1/133734 {by obliquely evaporated films, e.g. Si
phosphors illuminated by UV or blue	or SiO <sub>2</sub> films}
light}	1/133738 {for homogeneous alignment}
1/133615 {Edge-illuminating devices, i.e.	1/133742 {for homeotropic alignment}
illuminating from the side}	1/133746 {for high pretilt angles, i.e. higher than
1/133616 {Front illuminating devices}	15 degrees}
1/133617 {Illumination with ultraviolet light;	1/133749 {for low pretilt angles, i.e. lower than 15
Luminescent elements or materials	degrees}
associated to the cell}	1/133753 • • • • • { with different alignment orientations or pretilt angles on a same surface, e.g. for
1/133618 {for ambient light}	grey scale or improved viewing angle
1/13362 {providing polarized light, e.g. by	1/133757 { with different alignment
converting a polarisation component	orientations}
into another one }	1/133761 { with different pretilt angles}
	1/133765 {without a surface treatment}
	(

1/133769 • • • • • {comprising an active, e.g. switchable, alignment layer}	1/1347 Arrangement of liquid crystal layers or cells in which the final condition of one
1/133773 { the alignment material or treatment being different for the two opposite	light beam is achieved by the addition of the effects of two or more layers or cells
substrates} 1/133776 {having structures locally influencing the alignment, e.g. unevenness}	1/13471 {in which all the liquid crystal cells or layers remain transparent, e.g. FLC, ECB, DAP, HAN, TN, STN, SBE-LC
1/13378 {by treatment of the surface, e.g. embossing, rubbing or light irradiation (G02F 1/133711, G02F 1/133734,	cells (G02F 1/13475 takes precedence)}  1/13473 {for wavelength filtering or for colour display without the use of colour mosaic filters}
G02F 1/133753 take precedence)} 1/133784 {by rubbing}	1/13475 {in which at least one liquid crystal cell
1/133788 {by light irradiation, e.g. linearly polarised light photo-polymerisation}	or layer is doped with a pleochroic dye, e.g. GH-LC cell (G02F 1/13476 takes precedence)}
1/133792 {by etching}	1/13476 {in which at least one liquid crystal cell
1/133796 {having conducting property} 1/1339 Gaskets; Spacers; Sealing of cells	or layer assumes a scattering state}
1/13392 {spacers dispersed on the cell substrate,	1/13478 {based on selective reflection}
e.g. spherical particles, microfibres}	1/135 Liquid crystal cells structurally associated
1/13394 {spacers regularly patterned on the cell subtrate, e.g. walls, pillars	with a photoconducting or a ferro- electric layer, the properties of which can be optically or electrically varied
(G02F 1/133377 takes precedence)} 1/13396 {Spacers having different sizes}	$\{(\underline{G02F 1/133348} \text{ takes precedence})\}$
1/13398 {Spacer materials; Spacer properties}	1/1351 {Light-absorbing or blocking layers}
1/1341 Filling or closing of cells	1/1352 • • • • {Light-reflecting layers}
1/13415 {Drop filling process}	1/1354 {having a particular photoconducting
1/1343 Electrodes {(reflective electrodes G02F 1/133553)}	structure or material \\ 1/1355 \{\text{Materials or manufacture processes}\}\\ 1/1355 \(\text{Materials or manufacture processes}\)
1/134309 {characterised by their geometrical	thereof} 1/1357 {Electrode structure}
arrangement} 1/134318 {having a patterned common	1/1358 {the supplementary layer being a ferro- electric layer}
electrode} 1/134327 {Segmented, e.g. alpha numeric	1/136 Liquid crystal cells structurally associated
1/134327 {Segmented, e.g. alpha numeric display}	with a semi-conducting layer or substrate,
1/134327 {Segmented, e.g. alpha numeric	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit
1/134327 · · · · · {Segmented, e.g. alpha numeric display} 1/134336 · · · · · {Matrix} 1/134345 · · · · · {Subdivided pixels, e.g. for grey scale or redundancy}	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS]	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials therefor; method of making}	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}  1/136213 {Storage capacitors associated with the pixel electrode}  1/136218 {Shield electrodes}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials therefor; method of making}  1/1345 Conductors connecting electrodes to cell terminals	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}  1/136213 {Storage capacitors associated with the pixel electrode}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials therefor; method of making}  1/1345 {Conductors connecting electrodes to cell terminals}  1/13452 {Conductors connecting driver circuitry and terminals of panels}	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}  1/136213 {Storage capacitors associated with the pixel electrode}  1/136222 {Colour filters incorporated in the active matrix substrate}  1/136227 {Through-hole connection of the pixel}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials therefor; method of making}  1/1345 Conductors connecting electrodes to cell terminals  1/13452 {Conductors connecting driver circuitry and terminals of panels}  1/13454 {Drivers integrated on the active matrix substrate (G02F 1/136277 takes	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}  1/136213 {Storage capacitors associated with the pixel electrode}  1/136222 {Colour filters incorporated in the active matrix substrate}  1/136227 {Through-hole connection of the pixel electrode to the active element through an insulation layer}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials therefor; method of making}  1/1345 {Conductors connecting electrodes to cell terminals}  1/13454 {Drivers integrated on the active matrix substrate (G02F 1/136277 takes precedence)}	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}  1/136213 {Storage capacitors associated with the pixel electrode}  1/136222 {Colour filters incorporated in the active matrix substrate}  1/136227 {Through-hole connection of the pixel electrode to the active element through an insulation layer}  1/136231 {for reducing the number of lithographic}
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials therefor; method of making}  1/1345 {Conductors connecting electrodes to cell terminals}  1/13454 {Drivers integrated on the active matrix substrate (G02F 1/136277 takes precedence)}  1/13456 {Cell terminals located on one side of the display only}	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}  1/136213 {Storage capacitors associated with the pixel electrode}  1/136222 {Colour filters incorporated in the active matrix substrate}  1/136227 {Through-hole connection of the pixel electrode to the active element through an insulation layer}  1/136231 {for reducing the number of lithographic steps}  1/136236 {using a grey or half tone lithographic
1/134327 {Segmented, e.g. alpha numeric display}  1/134336 {Matrix}  1/134345 {Subdivided pixels, e.g. for grey scale or redundancy}  1/134354 {the sub-pixels being capacitively coupled}  1/134363 {for applying an electric field parallel to the substrate, i.e. in-plane switching [IPS]}  1/134372 {for fringe field switching [FFS] where the common electrode is not patterned}  1/134381 {Hybrid switching mode, i.e. for applying an electric field with components parallel and orthogonal to the substrates}  1/13439 {characterised by their electrical, optical, physical properties; materials therefor; method of making}  1/1345 {Conductors connecting electrodes to cell terminals}  1/13454 {Drivers integrated on the active matrix substrate (G02F 1/136277 takes precedence)}  1/13456 {Cell terminals located on one side of	with a semi-conducting layer or substrate, e.g. cells forming part of an integrated circuit (G02F 1/135 takes precedence)  1/13606 {having means for reducing parasitic capacitance}  1/13613 {the semiconductor element being formed on a first substrate and thereafter transferred to the final cell substrate}  1/1362 Active matrix addressed cells {(G02F 1/134336, G02F 1/134363 take precedence)}  1/136204 {Arrangements to prevent high voltage or static electricity failures}  1/136209 {Light shielding layers, e.g. black matrix, incorporated in the active matrix substrate, e.g. structurally associated with the switching element}  1/136213 {Storage capacitors associated with the pixel electrode}  1/136227 {Colour filters incorporated in the active matrix substrate}  1/136231 {Through-hole connection of the pixel electrode to the active element through an insulation layer}  1/136231 {for reducing the number of lithographic steps}

1/136245 {having complementary transistors}	1/1393 {the birefringence of the liquid crystal
1/13625 {Patterning using multi-mask exposure}	being electrically controlled, e.g. ECB-,
1/136254 {Checking; Testing}	DAP-, HAN-, PI-LC cells (G02F 1/1396,
1/136259 {Repairing; Defects}	$\underline{\text{G02F } 1/141}$ take precedence)}
1/136263 {Line defects}	1/1395 {Optically compensated birefringence
	[OCB]- cells or PI- cells}
1/136268 {Switch defects}	1/1396 {the liquid crystal being selectively
1/136272 • • • • • {Auxiliary lines}	controlled between a twisted state and
1/136277 {formed on a semiconductor substrate,	
e.g. of silicon}	a non-twisted state, e.g. TN-LC cell
1/136281 {having a transmissive semiconductor	(G02F 1/141  takes precedence)
substrate}	1/1397 {the twist being substantially higher
1/136286 {Wiring, e.g. gate line, drain line}	than 90°, e.g. STN-, SBE-, OMI-LC
	cells}
1/13629 {Multilayer wirings}	$1/1398$ {the twist being below $90^{\circ}$ }
1/136295 {Materials; Compositions;	1/141 using ferroelectric liquid crystals
Manufacture processes}	1/1412 {Antiferroelectric liquid crystals}
1/1365 in which the switching element is a two-	
electrode device {(G02F 1/136277 takes	1/1414 {Deformed helix ferroelectric [DHL]}
precedence)}	1/1416 {Details of the smectic layer structure,
1/1368 in which the switching element is a	e.g. bookshelf, chevron, C1 and C2}
three-electrode device {(G02F 1/136277	1/1418 (using smectic liquid crystals, e.g. based
takes precedence)}	on the electroclinic effect}
	1/15 based on an electrochromic effect
1/13685 {Top gates}	2001/1502 {complementary cell}
1/137 characterised by the electro-optical or	2001/15025 {having an inorganic electrochromic layer
magneto-optical effect, e.g. field-induced	
phase transition, orientation effect, guest-host	and a second solid organic electrochromic
interaction or dynamic scattering	layer}
1/13706 {the liquid crystal having positive dielectric	1/1503 • • • caused by oxidation-reduction reactions in
anisotropy}	organic liquid solutions, e.g. viologen solutions
1/13712 {the liquid crystal having negative dielectric	1/1506 caused by electrodeposition, e.g. electrolytic
anisotropy}	deposition of an inorganic material on or close
***	to an electrode
1/13718 {based on a change of the texture state of a	1/1508 {using a solid electrolyte}
cholesteric liquid crystal}	
1/13725 {based on guest-host interaction	, , , , , , , , , , , , , , , , , , ,
( <u>G02F 1/13762</u> , <u>G02F 1/13737</u> , take	e.g. by the electrodeposited material
precedence)}	2001/15145 {the electrochromic layer comprises a
1/13731 {based on a field-induced phase transition	mixture of anodic and cathodic compounds}
( <u>G02F 1/13781</u> takes precedence)}	1/1516 comprising organic material
1/13737 {in liquid crystals doped with a pleochroic	1/15165 {Polymers}
dye}	2001/1517 {Cyano complex compounds, e.g. Prussian
	blue}
1/13743 {based on electrohydrodynamic instabilities	
or domain formation in liquid crystals}	
1/1375 {using dynamic scattering}	1/1523 comprising inorganic material
1/13756 {the liquid crystal selectively	1/1524 Transition metal compounds
assuming a light-scattering state	1/15245 {based on iridium oxide or hydroxide}
(G02F 1/1334, G02F 1/13718 take	1/1525 {characterised by a particular ion
precedence)}	transporting layer, e.g. electrolyte}
1/13762 {containing luminescent or	1/153 Constructional details
electroluminescent additives}	
1/13768 {based on magneto-optical effects}	1/1533 { structural features not otherwise provided
	for}
1/13775 {Polymer-stabilized liquid crystal layers}	2001/1536 {additional, e.g. protective, layer inside the
1/13781 • • • • {using smectic liquid crystals ( <u>G02F 1/141</u>	cell}
takes precedence)}	1/155 Electrodes
1/13787 {Hybrid-alignment cells (G02F 1/1393 takes	2001/1552 {Inner electrode, e.g. the electrochromic
precedence)}	layer being sandwiched between the inner
1/13793 {Blue phases}	electrode and the support substrate}
liquid crystal remains transparent	2001/1557 {Side by side arrangements of working
1/1391 {Bistable or multi-stable liquid crystal	and counter electrodes}
cells ( $\underline{G02F 1/141}$ takes precedence)}	1/157 Structural association of cells with optical
1/1392 {using a field-induced sign-reversal of the	devices, e.g. reflectors or illuminating
dielectric anisotropy}	devices
10,	1/161 Gaskets; Spacers; Sealing of cells; Filling or
	closing of cells
	or comp

1/163	Operation of electrochromic cells, e.g.	1/225	. in an optical waveguide structure
	electrodeposition cells; Circuit arrangements		• • {in optical fibres}
	therefor		• • {controlled by a high-frequency
2001/1635	• • • { the pixel comprises active switching elements, e.g. TFT}		electromagnetic component in an electric
2001/164		1/0057	waveguide structure}
2001/164 1/165	<ul><li> {the electrolyte is made of polymers}</li><li>. based on translational movement of particles in a</li></ul>	1/2257	• • {the optical waveguides being made of semiconducting material}
	fluid under the influence of an applied field	1/23	for the control of the colour
1/166	characterised by the electro-optical or magneto-		( <u>G02F 1/03</u> - <u>G02F 1/21</u> take precedence)
	optical effect		. as to hue or predominant wavelength
1/167	by electrophoresis		or the control of the position or the direction of
1/1671	involving dry toners		ght beams, i.e. deflection
1/1673	by magnetophoresis		{Two-dimensional analogue deflection}
1/1675	Constructional details	1/292	{by controlled diffraction or phased-array
1/16753			beam steering (controlled diffraction for optical
1/1/755	e.g. frames or bezels	1/293	switching G02F 1/31)}
1/16755		1/295	{by another light beam, i.e. opto-optical deflection}
	Insulating layers	1/294	{Variable focal length devices}
	Microcapsules		{Analog deflection from or} in an optical
1/1676	Electrodes	1/293 • •	waveguide structure]
1/16/61	Side-by-side arrangement of working electrodes and counter-electrodes	1/2955	• {by controlled diffraction or phased-array
1/16760		1/2/33	beam steering (controlled diffraction for optical
	<ul><li> having three or more electrodes per pixel</li><li> for active matrices</li></ul>		waveguide switching G02F 1/313)}
1/16766		1/31	Digital deflection, {i.e. optical
1/1677	Structural association of cells with optical devices, e.g. reflectors or illuminating		switching}(G02F 1/33 takes precedence)
	devices devices	1/311	• {Cascade arrangement of plural switches}
2001/1678		1/313	. in an optical waveguide structure
2001/10/0	type}	1/3131	• { in optical fibres }
1/1679	Gaskets; Spacers; Sealing of cells; Filling or	1/3132	• • {of directional coupler type}
	closing of cells	1/3133	• • • {the optical waveguides being made of
1/1681	having two or more microcells partitioned		semiconducting materials}
	by walls, e.g. of microcup type	1/3134	• • {controlled by a high-frequency
1/1685	Operation of cells; Circuit arrangements		electromagnetic wave component in an
	affecting the entire cell		electric waveguide structure}
1/169	based on orientable non-spherical particles having		• • • {Vertical structure}
	a common optical characteristic, e.g. suspended		• • {of interferometric switch type}
1/15	particles of reflective metal flakes	1/3137	• • {with intersecting or branching waveguides,
1/17	based on variable-absorption elements not	1/2120	e.g. X-switches and Y-junctions}
1/170	provided for in groups G02F 1/015 - G02F 1/169	1/3138	• • • {the optical waveguides being made of semiconducting materials}
1/172	<ul> <li>• {based on a suspension of orientable dipolar particles, e.g. suspended particles displays}</li> </ul>	1/315	<ul> <li>based on the use of controlled internal</li> </ul>
1/174	• • {based on absorption band-shift, e.g. Stark - or	1/313 • •	reflection
1/1/4	Franz-Keldysh effect (G02F 1/015, G02F 1/178	1/33	Acousto-optical deflection devices {(circuit or
	take precedence)}	1/33	control arrangements therefor G02F 1/113)}
1/176	• • {using acid- based indicators}	1/332	• {comprising a plurality of transducers on the
1/178	• • • {based on pressure effects (G02F 1/195 takes		same crystal surface, e.g. multi-channel Bragg
	precedence)}		cell}
1/19	based on variable-reflection or variable-	1/335	. having an optical waveguide structure
	refraction elements not provided for in groups	1/35 . N	Non-linear optics
	<u>G02F 1/015</u> - <u>G02F 1/169</u>	1/3501	{Constructional details or arrangements of non-
1/195	• • • {by using frustrated reflection (digital		linear optical devices, e.g. shape of non-linear
	reflection using controlled total internal		crystals}
4 (2.4	reflection <u>G02F 1/315</u> )}	1/3503	• {Structural association of optical elements, e.g.
1/21	• by interference	1/2505	lenses, with the non-linear optical device}
1/211	{Sagnac type}		• {Coatings; Housings; Supports}
1/212	{Mach-Zehnder type}	1/3507	<ul> <li>{Arrangements comprising two or more nonlinear optical devices}</li> </ul>
1/213	{Fabry-Perot type}	1/3509	• {Shape, e.g. shape of end face}
1/215	{Michelson type}		{Snape, e.g. snape of end race} {Self-focusing or self-trapping of light; Light-
1/216	<ul> <li>• {using liquid crystals, e.g. liquid crystal Fabry- Perot filters}</li> </ul>	1/3311 • •	induced birefringence; Induced optical Kerr-
1/217	{Multimode interference type}		effect}
1/217	<ul><li> {withinfode interference type}</li><li> {using semi-conducting materials}</li></ul>	1/3513	• {Soliton propagation}
1,210	(aning serial conducting materials)		

1/3515	• • {All-optical modulation, gating, switching,	1/37	• • for second-harmonic generation {(G02F 1/3532
2,000	e.g. control of a light beam by another light	-,	takes precedence)}
	beam (G02F 1/353, G02F 1/37, G02F 1/39 take	1/372	• • • {Means for homogenizing the output beam}
	precedence)}	1/374	• • • {Cherenkov radiation}
1/3517	• • · {using an interferometer}	1/377	in an optical waveguide structure
1/3519	• • • • {of Sagnac type, i.e. nonlinear optical loop mirror [NOLM]}	1/3775	• • • • { with a periodic structure, e.g. domain inversion, for quasi-phase-matching [QPM]
1/3521	{using a directional coupler}	4 (0.00	(G02F 1/383 takes precedence)}
1/3523	<ul> <li>{Non-linear absorption changing by light, e.g. bleaching}</li> </ul>	1/383	• • • of the optical fibre type
1/3525	• {Optical damage}	1/39	for parametric generation or amplification of light, infrared or ultraviolet waves
1/3525	<ul> <li>(optical damage)</li> <li>(using two-photon emission or absorption)</li> </ul>	1/392	Parametric amplification
1,3320	processes}	1/395	• • {I atanetic amplification} • • • {in optical waveguides}
1/3528	{for producing a supercontinuum}	1/397	• • • (Amplification of light by wave mixing
1/353	• • {Frequency conversion, i.e. wherein a light beam		involving an interference pattern, e.g. using
	is generated with frequency components different		photorefractive material}
	from those of the incident light beams}	2/00	Demodulating light; Transferring the modulation
1/3532	{Arrangements of plural nonlinear devices	2/00	of modulated light; Frequency-changing of light
	for generating multi-colour light beams, e.g. arrangements of SHG, SFG, OPO devices for		(G02F 1/35 takes precedence)
	generating RGB light beams}	2/002	• {using optical mixing}
1/3534	• • • {Three-wave interaction, e.g. sum-difference	2/004	• {Transferring the modulation of modulated light,
	frequency generation (G02F 1/3532 takes		i.e. transferring the information from one optical
	precedence)}		carrier of a first wavelength to a second optical
1/3536	• • • {Four-wave interaction}		carrier of a second wavelength, e.g. all-optical wavelength converter}
1/3538	• • • • {for optical phase conjugation (controlling	2/006	. {All-optical wavelength conversion}
	the intensity, frequency, phase, polarisation	2/008	Opto-electronic wavelength conversion, i.e.
	or direction of the emitted radiation using optical phase conjugation <u>H01S 3/10076</u> )}	2,000	involving photo-electric conversion of the first
1/354	{Third or higher harmonic generation}		optical carrier}
1/3542	{Multipass arrangements, i.e. arrangements	2/02	. Frequency-changing of light, e.g. by quantum
1,00.2	to make light pass multiple times through		counters
	the same element, e.g. using an enhancement	3/00	Optical logic elements; Optical bistable devices
	, , , , , , , , , , , , , , , , , , ,	.)/ UU	Oblical logic elements. Oblical bistable devices
	cavity}	3/02	Optical bistable devices
1/3544	<ul><li>cavity}</li><li> {Particular phase matching techniques}</li></ul>		
1/3544 1/3546	<ul><li>cavity}</li><li>• {Particular phase matching techniques}</li><li>• • {Active phase matching, e.g. by electro- or</li></ul>	3/02 3/022	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> </ul>
1/3546	<ul><li>cavity}</li><li>. {Particular phase matching techniques}</li><li>. {Active phase matching, e.g. by electro- or thermo-optic tuning}</li></ul>	3/02	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-</li> </ul>
	<ul> <li>cavity}</li> <li>. • {Particular phase matching techniques}</li> <li>. • • {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li>. • • {Quasi phase matching [QPM], e.g. using a</li> </ul>	3/02 3/022	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes</li> </ul>
1/3546 1/3548	<ul> <li>cavity}</li> <li>. • {Particular phase matching techniques}</li> <li>. • • {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li>. • • {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> </ul>	3/02 3/022 3/024	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> </ul>
1/3546	<ul> <li>cavity}</li> <li>. • {Particular phase matching techniques}</li> <li>. • • {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li>. • • {Quasi phase matching [QPM], e.g. using a</li> </ul>	3/02 3/022 3/024 3/026	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>• {based on laser effects}</li> </ul>
1/3546 1/3548 1/355	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li> {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li> {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li> characterised by the materials used</li> </ul>	3/02 3/022 3/024	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices</li> </ul>
1/3546 1/3548 1/355 1/3551	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li> {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li> {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li> {Crystals}</li> <li> {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As,</li> </ul>	3/02 3/022 3/024 3/026 3/028	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li>. {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li>. {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li>. {Crystals}</li> <li>. {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP}</li> </ul>	3/02 3/022 3/024 3/026	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li>. {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li>. {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li>. {Crystals}</li> <li>. {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP}</li> <li>. {Glasses}</li> </ul>	3/02 3/022 3/024 3/026 3/028	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li>. {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li>. {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li>. {Crystals}</li> <li>. {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP}</li> <li>. {Glasses}</li> <li>. {Semiconductor materials, e.g. quantum wells}</li> </ul>	3/02 3/022 3/024 3/026 3/028	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>• {based on laser effects}</li> <li>• {based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li> {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li> {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li>. {Crystals}</li> <li> {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP}</li> <li> {Glasses}</li> <li> {Semiconductor materials, e.g. quantum wells}</li> <li> {Poled materials, e.g. with periodic poling;</li> </ul>	3/02 3/022 3/024 3/026 3/028	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li> {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li> {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li>. {Crystals}</li> <li> {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP}</li> <li> {Glasses}</li> <li> {Semiconductor materials, e.g. quantum wells}</li> <li> {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g.</li> </ul>	3/02 3/022 3/024 3/026 3/028	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li> {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li> {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li>. {Crystals}</li> <li> {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP}</li> <li> {Glasses}</li> <li> {Semiconductor materials, e.g. quantum wells}</li> <li> {Poled materials, e.g. with periodic poling;</li> </ul>	3/02 3/022 3/024 3/026 3/028 <b>7/00</b>	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> </ul> Optical analogue/digital converters NOTE This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558	<ul> <li>cavity}</li> <li>. {Particular phase matching techniques}</li> <li>. {Active phase matching, e.g. by electro- or thermo-optic tuning}</li> <li>. {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure}</li> <li>. characterised by the materials used</li> <li>. {Crystals}</li> <li>. {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP}</li> <li>. {Glasses}</li> <li>. {Semiconductor materials, e.g. quantum wells}</li> <li>. {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]}</li> </ul>	3/02 3/022 3/024 3/026 3/028	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom}	3/02 3/022 3/024 3/026 3/028 7/00	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558 1/3611 1/3611 1/3612 1/3613	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {containing Sulfur}	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> <b>2201/00</b> 2201/02	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558 1/3611 1/3612 1/3613 1/3614	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Heterocycles having S as heteroatom}	3/02 3/022 3/024 3/026 3/028 7/00	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>fibre</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558 1/3611 1/3612 1/3613 1/3614 1/3615	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Heterocycles having S as heteroatom} {Containing polymers}	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> 2201/00 2201/02 2201/04	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>• {based on laser effects}</li> <li>• {based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>• fibre</li> <li>• monomode</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558 1/3611 1/3612 1/3613 1/3614	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Containing Sulfur} {Heterocycles having S as heteroatom} {containing polymers} {having the non-linear optical group in the	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> <b>2201/00</b> 2201/02 2201/04 2201/05	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>• {based on laser effects}</li> <li>• {based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>• fibre</li> <li>• monomode</li> <li>• multimode</li> <li>• integrated waveguide</li> <li>• ridge; rib; strip loaded</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558 1/361 1/3611 1/3612 1/3613 1/3614 1/3615 1/3616	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Heterocycles having S as heteroatom} {containing polymers} {having the non-linear optical group in the main chain}	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> <b>2201/00</b> 2201/02 2201/04 2201/05 2201/06	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>fibre</li> <li>monomode</li> <li>multimode</li> <li>integrated waveguide</li> <li>ridge; rib; strip loaded</li> <li>channel; buried</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558 1/3611 1/3612 1/3613 1/3614 1/3615	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Heterocycles having S as heteroatom} {Aving the non-linear optical group in the main chain} {having the non-linear optical group in a	3/02 3/022 3/024 3/024 3/028 <b>7/00</b> <b>2201/00</b> 2201/02 2201/04 2201/05 2201/06 2201/063 2201/066 2201/07	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>fibre</li> <li>monomode</li> <li>multimode</li> <li>integrated waveguide</li> <li>ridge; rib; strip loaded</li> <li>channel; buried</li> <li>buffer layer</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3556 1/3558 1/3611 1/3612 1/3613 1/3614 1/3615 1/3616	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Containing Sulfur} {Heterocycles having S as heteroatom} {containing polymers} {having the non-linear optical group in the main chain} {having the non-linear optical group in a side chain}	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> <b>2201/00</b> 2201/02 2201/04 2201/05 2201/06 2201/063 2201/066 2201/07 2201/08	<ul> <li>Optical bistable devices</li> <li>{based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>{based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>{based on laser effects}</li> <li>{based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>fibre</li> <li>monomode</li> <li>multimode</li> <li>integrated waveguide</li> <li>ridge; rib; strip loaded</li> <li>channel; buried</li> <li>buffer layer</li> <li>light absorbing layer</li> </ul>
1/3546 1/3548 1/355 1/3551 1/3553 1/3555 1/3556 1/3558 1/361 1/3611 1/3612 1/3613 1/3614 1/3615 1/3616	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Heterocycles having S as heteroatom} {Aving the non-linear optical group in the main chain} {having the non-linear optical group in a	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> <b>2201/00</b> 2201/02 2201/04 2201/05 2201/06 2201/06 2201/06 2201/07 2201/08 2201/08	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>• {based on laser effects}</li> <li>• {based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>• fibre</li> <li>• monomode</li> <li>• multimode</li> <li>• integrated waveguide</li> <li>• channel; buried</li> <li>• buffer layer</li> <li>• light absorbing layer</li> <li>• infrared absorbing</li> </ul>
1/3546  1/3548  1/3551 1/3551 1/3553  1/3555 1/3556 1/3558  1/3611 1/3611 1/3612 1/3613 1/3614 1/3615 1/3616  1/3617	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {Containing Sulfur} {Heterocycles having S as heteroatom} {having the non-linear optical group in the main chain} {having the non-linear optical group in a side chain} {Langmuir Blodgett Films}	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> <b>2201/00</b> 2201/02 2201/04 2201/05 2201/06 2201/06 2201/06 2201/08 2201/08 2201/08	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>• {based on laser effects}</li> <li>• {based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>• fibre</li> <li>• monomode</li> <li>• multimode</li> <li>• integrated waveguide</li> <li>• ridge; rib; strip loaded</li> <li>• channel; buried</li> <li>• buffer layer</li> <li>• light absorbing layer</li> <li>• infrared absorbing</li> <li>• UV absorbing</li> </ul>
1/3546  1/3548  1/3548  1/355  1/3551  1/3553  1/3555  1/3556  1/3558  1/3611  1/3611  1/3612  1/3613  1/3614  1/3615  1/3616  1/3617  1/3618  1/3619	cavity} {Particular phase matching techniques} {Active phase matching, e.g. by electro- or thermo-optic tuning} {Quasi phase matching [QPM], e.g. using a periodic domain inverted structure} characterised by the materials used {Crystals} {having the formula MTiOYO4, where M=K, Rb, TI, NH4 or Cs and Y=P or As, e.g. KTP} {Glasses} {Semiconductor materials, e.g. quantum wells} {Poled materials, e.g. with periodic poling; Fabrication of domain inverted structures, e.g. for quasi-phase-matching [QPM]} Organic materials {containing Nitrogen} {Heterocycles having N as heteroatom} {containing Sulfur} {Heterocycles having S as heteroatom} {having the non-linear optical group in the main chain} {having the non-linear optical group in a side chain} {Corganometallic compounds}	3/02 3/022 3/024 3/026 3/028 <b>7/00</b> <b>2201/00</b> 2201/02 2201/04 2201/05 2201/06 2201/06 2201/06 2201/07 2201/08 2201/08	<ul> <li>Optical bistable devices</li> <li>• {based on electro-, magneto- or acousto-optical elements (G02F 3/028 takes precedence)}</li> <li>• {based on non-linear elements, e.g. non-linear Fabry-Perot cavity (G02F 3/028 takes precedence)}</li> <li>• {based on laser effects}</li> <li>• {based on self electro-optic effect devices [SEED]}</li> <li>Optical analogue/digital converters</li> <li>NOTE</li> <li>This group covers only converters based in substantial manner on elements which are provided for in group G02F 1/00.</li> <li>Constructional arrangements not provided for in groups G02F 1/00 - G02F 7/00</li> <li>• fibre</li> <li>• monomode</li> <li>• multimode</li> <li>• integrated waveguide</li> <li>• channel; buried</li> <li>• buffer layer</li> <li>• light absorbing layer</li> <li>• infrared absorbing</li> </ul>

2202/04 . dye

2201/122	having a particular pattern	2202/043	pleochroic
2201/123	pixel	2202/046	fluorescent
2201/124	interdigital	2202/06	• dopant
2201/125	• delta-beta	2202/07	• poled
2201/126	push-pull	2202/08	glass transition temperature
			-
2201/127	travelling wave	2202/09	• inorganic glass
2201/128	field shaping	2202/10	• semiconductor
2201/14	• asymmetric	2202/101	Ga×As and alloy
2201/15	• periodic	2202/102	In×P and alloy
2201/16	• series; tandem	2202/103	a-Si
2201/17	Multi-pass arrangements, i.e. arrangements to pass	2202/104	poly-Si
	light a plurality of times through the same element,	2202/105	single crystal Si
	e.g. by using an enhancement cavity	2202/106	Cd×Se or Cd×Te and alloys
2201/18	• parallel	2202/107	Zn×S or Zn×Se and alloys
2201/20	• delay line	2202/108	quantum wells
2201/205	• of fibre type	2202/108	
2201/203	grating		• photoconductor
2201/30	. grating coupler	2202/13	• photorefractive
		2202/14	• photochromic
2201/305	diffraction grating	2202/16	. conductive
2201/307	Reflective grating, i.e. Bragg grating	2202/20	• LiNbO <sub>3</sub> , LiTaO <sub>3</sub>
2201/34	. reflector	2202/22	Antistatic materials or arrangements
2201/343	cholesteric liquid crystal reflector	2202/28	Adhesive materials or arrangements
2201/346	distributed (Bragg) reflector	2202/30	Metamaterials
2201/36	Airflow channels, e.g. constructional arrangements	2202/32	Photonic crystals
	facilitating the flow of air	2202/34	Metal hydrides materials
2201/38	Anti-reflection arrangements	2202/34	Micro- or nanomaterials
2201/40	Arrangements for improving the aperture ratio		
2201/42	Arrangements for providing conduction through an	2202/38	Sol-gel materials
2201/42	insulating substrate	2202/40	Materials having a particular birefringence,
2201/44	Arrangements combining different electro-active		retardation
2201/44	layers, e.g. electrochromic, liquid crystal or	2202/42	Materials having a particular dielectric constant
		2203/00	Function characteristic
2201/46	electroluminescent layers	<b>2203/00</b>	Function characteristic
2201/46	electroluminescent layers  • Fixing elements	2203/01	. transmissive
2201/465	electroluminescent layers  Fixing elements  Snap -fit	2203/01 2203/02	<ul><li>transmissive</li><li>reflective</li></ul>
2201/465 2201/48	electroluminescent layers  Fixing elements  Snap -fit Flattening arrangements	2203/01 2203/02 2203/023	<ul><li>transmissive</li><li>reflective</li><li>total internal reflection</li></ul>
2201/465 2201/48 2201/50	electroluminescent layers  Fixing elements  Snap -fit Flattening arrangements Protective arrangements	2203/01 2203/02 2203/023 2203/026	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> </ul>
2201/465 2201/48	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions	2203/01 2203/02 2203/023 2203/026 2203/03	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> </ul>
2201/465 2201/48 2201/50	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> </ul>
2201/465 2201/48 2201/50 2201/501	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions	2203/01 2203/02 2203/023 2203/026 2203/03	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503	electroluminescent layers  Fixing elements  Snap -fit Flattening arrangements Protective arrangements Blocking layers, e.g. against migration of ions Arrangements improving the resistance to shock Arrangements improving the resistance to acoustic resonance like noise	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/055 2203/06	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/055 2203/06 2203/07	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508 2201/52 2201/54 2201/56	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/13 2203/15	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508 2201/52 2201/54 2201/56	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/13 2203/15	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508 2201/52 2201/54 2201/56	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508 2201/52 2201/54 2201/56 2201/58	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/07 2203/07 2203/10 2203/11 2203/12 2203/15 2203/16 2203/17	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/506 2201/508  2201/52 2201/54 2201/56  2201/58  2202/00 2202/01	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/506 2201/508  2201/52 2201/54 2201/56 2201/58  2202/00 2202/01 2202/02	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> <li>Intrinsic phase difference, i.e. optical bias, of an</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508  2201/52 2201/54 2201/56 2201/58  2202/00 2202/01 2202/02 2202/021	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material  low molecular weight	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18 2203/19	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508  2201/52 2201/54 2201/56 2201/58  2202/00 2202/01 2202/02 2202/021 2202/022	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material  low molecular weight  polymeric	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18 2203/19	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> <li>Intrinsic phase difference, i.e. optical bias, of an</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508  2201/52 2201/54 2201/56 2201/58  2202/00 2202/01 2202/02 2202/021 2202/023	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material  low molecular weight  polymeric  curable	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18 2203/19	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> <li>Intrinsic phase difference, i.e. optical bias, of an optical modulator; Methods for the pre-set thereof</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508  2201/52 2201/54 2201/56 2201/58  2202/00 2202/01 2202/02 2202/021 2202/023 2202/025	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material  low molecular weight  polymeric  curable  thermocurable	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18 2203/19	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> <li>Intrinsic phase difference, i.e. optical bias, of an optical modulator; Methods for the pre-set thereof</li> <li>Thermal instability, i.e. DC drift, of an optical</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508  2201/52 2201/54 2201/56 2201/58  2202/00 2202/01 2202/02 2202/021 2202/025 2202/026	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material  low molecular weight  polymeric  curable  charge transfer complex	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18 2203/19	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> <li>Intrinsic phase difference, i.e. optical bias, of an optical modulator; Methods for the pre-set thereof</li> <li>Thermal instability, i.e. DC drift, of an optical modulator; Arrangements or methods for the</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/506 2201/508  2201/52 2201/54 2201/56  2201/58  2202/00 2202/01 2202/02 2202/021 2202/025 2202/025 2202/027	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material  low molecular weight  polymeric  curable  charge transfer complex  Langmuir-Blodgett film	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18 2203/19 2203/20	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> <li>Intrinsic phase difference, i.e. optical bias, of an optical modulator; Methods for the pre-set thereof</li> <li>Thermal instability, i.e. DC drift, of an optical modulator; Arrangements or methods for the reduction thereof</li> </ul>
2201/465 2201/48 2201/50 2201/501 2201/503 2201/505 2201/506 2201/508  2201/52 2201/54 2201/56 2201/58  2202/00 2202/01 2202/02 2202/021 2202/025 2202/026	electroluminescent layers  Fixing elements  Snap -fit  Flattening arrangements  Protective arrangements  Blocking layers, e.g. against migration of ions  Arrangements improving the resistance to shock  Arrangements improving the resistance to acoustic resonance like noise  Repairing, e.g. with redundant arrangement against defective part  Pseudo repairing, e.g. a defective part is brought into a condition in which it does not disturb the functioning of the device  RGB geometrical arrangements  Arrangements for reducing warping-twist  Substrates having a particular shape, e.g. non-rectangular  Arrangements comprising a monitoring photodetector  Materials and properties  dipole  organic material  low molecular weight  polymeric  curable  charge transfer complex	2203/01 2203/02 2203/023 2203/026 2203/03 2203/04 2203/05 2203/05 2203/06 2203/07 2203/09 2203/10 2203/11 2203/12 2203/13 2203/15 2203/16 2203/17 2203/18 2203/19 2203/20 2203/21	<ul> <li>transmissive</li> <li>reflective</li> <li>total internal reflection</li> <li>attenuated or frustrated internal reflection</li> <li>scattering</li> <li>wavelength independent</li> <li>wavelength dependent</li> <li>wavelength filtering</li> <li>Polarisation independent</li> <li>Polarisation dependent</li> <li>transflective</li> <li>plasmon</li> <li>involving infrared radiation</li> <li>spatial light modulator</li> <li>involving THZ radiation</li> <li>involving resonance effects, e.g. resonantly enhanced interaction</li> <li>involving spin polarization effects</li> <li>involving soliton waves</li> <li>adaptive optics, e.g. wavefront correction</li> <li>linearised modulation; reduction of harmonic distortions</li> <li>Intrinsic phase difference, i.e. optical bias, of an optical modulator; Methods for the pre-set thereof</li> <li>Thermal instability, i.e. DC drift, of an optical modulator; Arrangements or methods for the reduction thereof</li> <li>diffractive</li> </ul>

2203/25	Frequency chirping of an optical modulator;
	Arrangements or methods for the pre-set or tuning thereof
2203/255	Negative chirp
2203/26	• Pulse shaping; Apparatus or methods therefor
2203/28	• focussing or defocussing
2203/30	. Gray scale
2203/34	Colour display without the use of colour mosaic
	filters
2203/48	Variable attenuator
2203/50	Phase-only modulation
2203/52	Optical limiters
2203/54	Optical pulse train (comb) synthesizer
2203/56	. Frequency comb synthesizer
2203/58	• Multi-wavelength, e.g. operation of the device at a
	plurality of wavelengths
2203/585	Add/drop devices
2203/60	Temperature independent
2203/62	Switchable arrangements whereby the element
	being usually not switchable
2203/64	• Normally black display, i.e. the off state being black
2203/66	. Normally white display, i.e. the off state being white
2203/68	Green display, e.g. recycling, reduction of harmful
	substances
2203/69	• Arrangements or methods for testing or calibrating a
	device
	Semiconductor optical amplifier [SOA] used in a
2203/70	
2203/70	device covered by G02F
2413/00	
	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical
	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number,
	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation
2413/00	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates
<b>2413/00</b> 2413/01	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1
2413/00 2413/01 2413/02	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2
2413/00 2413/01 2413/02 2413/03	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3
2413/00 2413/01 2413/02 2413/03 2413/04	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4  Single plate on one side of the LC cell
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4  Single plate on one side of the LC cell  Two plates on one side of the LC cell
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4  Single plate on one side of the LC cell  Two plates on one side of the LC cell
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/08	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4  Single plate on one side of the LC cell  Two plates on one side of the LC cell  All plates on one side of the LC cell  with a particular optical axis orientation
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4  Single plate on one side of the LC cell  Two plates on one side of the LC cell  All plates on one side of the LC cell  with a particular optical axis orientation  with refractive index ellipsoid inclined, or tilted,
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/08 2413/10	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1 Number of plates being 2 Number of plates being 3 Number of plates greater than or equal to 4 Single plate on one side of the LC cell Two plates on one side of the LC cell All plates on one side of the LC cell with a particular optical axis orientation with refractive index ellipsoid inclined, or tilted, relative to the LC-layer surface O plate
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/08	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4  Single plate on one side of the LC cell  Two plates on one side of the LC cell  All plates on one side of the LC cell  with a particular optical axis orientation  with refractive index ellipsoid inclined, or tilted,
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/08 2413/10 2413/105	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1 Number of plates being 2 Number of plates being 3 Number of plates greater than or equal to 4 Single plate on one side of the LC cell Two plates on one side of the LC cell All plates on one side of the LC cell with a particular optical axis orientation with refractive index ellipsoid inclined, or tilted, relative to the LC-layer surface O plate  with varying inclination in thickness direction, e.g. hybrid oriented discotic LC Biaxial compensators
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/10 2413/10 2413/10 2413/13	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1 Number of plates being 2 Number of plates being 3 Number of plates greater than or equal to 4 Single plate on one side of the LC cell Two plates on one side of the LC cell All plates on one side of the LC cell with a particular optical axis orientation with refractive index ellipsoid inclined, or tilted, relative to the LC-layer surface O plate  with varying inclination in thickness direction, e.g. hybrid oriented discotic LC Biaxial compensators Positive birefingence
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/08 2413/10 2413/105	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1 Number of plates being 2 Number of plates being 3 Number of plates greater than or equal to 4 Single plate on one side of the LC cell Two plates on one side of the LC cell All plates on one side of the LC cell with a particular optical axis orientation with refractive index ellipsoid inclined, or tilted, relative to the LC-layer surface O plate  with varying inclination in thickness direction, e.g. hybrid oriented discotic LC Biaxial compensators Positive birefingence Negative birefingence
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/10 2413/10 2413/10 2413/13	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1  Number of plates being 2  Number of plates being 3  Number of plates greater than or equal to 4  Single plate on one side of the LC cell  Two plates on one side of the LC cell  All plates on one side of the LC cell  with a particular optical axis orientation  with refractive index ellipsoid inclined, or tilted, relative to the LC-layer surface O plate  with varying inclination in thickness direction, e.g. hybrid oriented discotic LC  Biaxial compensators  Positive birefingence  Negative birefingence  with twisted orientation, e.g. comprising helically
2413/00 2413/01 2413/02 2413/03 2413/04 2413/05 2413/06 2413/07 2413/10 2413/10 2413/10 2413/12 2413/13 2413/14	device covered by G02F  Indexing scheme related to G02F 1/13363, i.e. to birefringent elements, e.g. for optical compensation, characterised by the number, position, orientation or value of the compensation plates  Number of plates being 1 Number of plates being 2 Number of plates being 3 Number of plates greater than or equal to 4 Single plate on one side of the LC cell Two plates on one side of the LC cell All plates on one side of the LC cell with a particular optical axis orientation with refractive index ellipsoid inclined, or tilted, relative to the LC-layer surface O plate  with varying inclination in thickness direction, e.g. hybrid oriented discotic LC Biaxial compensators Positive birefingence Negative birefingence